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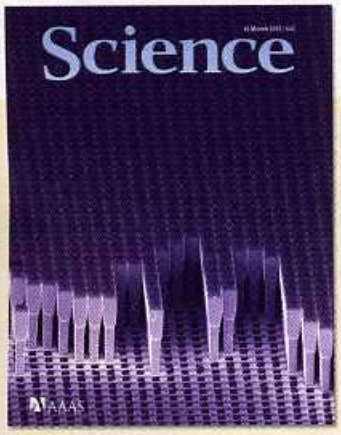
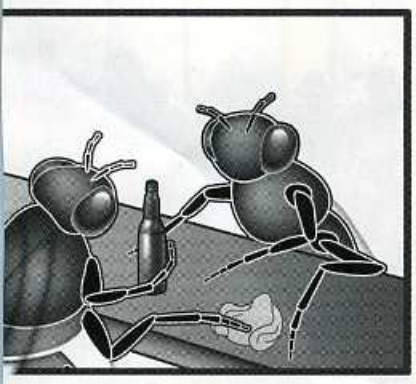


COVER

False-colored scanning electron micrograph of ~8-micrometer-tall germanium crystals, separated by finite gaps, grown onto silicon pillars. In structures like this one, wafer bowing and layer cracking are absent, allowing single-crystal integration of different materials onto a silicon substrate, which serves as a platform for many applications, such as multiple-junction solar cells, x-ray and particle detectors, or power electronic devices. See page 1330.

Image: Claudiu V. Falub, Laboratory for Solid State Physics, Swiss Federal Institute of Technology (ETH-Zürich)

DEPARTMENTS



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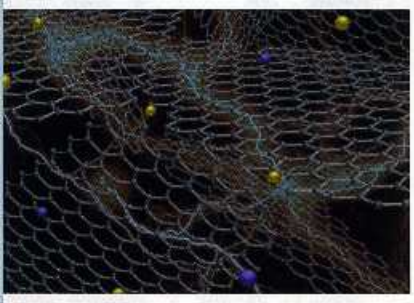

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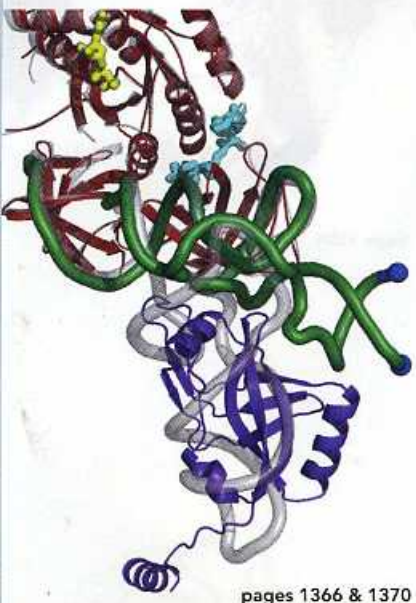

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CREDITS: (MIDDLE) IMAGE DESIGNED BY JONATHAN K. WASSEL, UCLA